



PSMN1R4-40YSH

N-channel 40 V, 1.4 mOhm, 240 A standard level MOSFET in LFPAK56 using NextPower-S3 Schottky-Plus technology

18 October 2023

Product data sheet

1. General description

240 A, standard level gate drive N-channel enhancement mode MOSFET in 175 °C LFPAK56 package using advanced TrenchMOS Superjunction technology. This product has been designed and qualified for high performance power switching applications.

2. Features and benefits

- 240 A continuous $I_{D(max)}$ rating
- Avalanche rated, 100% tested at $I_{AS} = 190$ A
- Strong SOA (linear-mode) rating
- NextPower-S3 technology delivers 'superfast switching with soft body-diode recovery'
- Low Q_{RR} , Q_G and Q_{GD} for high system efficiency and low EMI designs
- Schottky-Plus body-diode with low V_{SD} , low Q_{RR} , soft recovery and low I_{DSS} leakage
- High reliability LFPAK (Power SO8) package, with copper-clip and solder die attach, qualified to 175 °C
- Exposed leads can be wave soldered, visual solder joint inspection and high quality solder joints
- Low parasitic inductance and resistance

3. Applications

- High-performance synchronous rectification
- DC-to-DC converters
- High performance and high efficiency server power supply
- Brushless DC motor control
- Battery protection
- Load-switch and eFuse
- Inrush management, hotswap

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------------|----------------------------------|---|-----|------|-----|------|
| V_{DS} | drain-source voltage | $25\text{ °C} \leq T_j \leq 175\text{ °C}$ | - | - | 40 | V |
| I_D | drain current | $V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2 | [1] | - | 240 | A |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ °C}$; Fig. 1 | - | - | 333 | W |
| T_j | junction temperature | | -55 | - | 175 | °C |
| Static characteristics | | | | | | |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10 | - | 1.06 | 1.4 | mΩ |

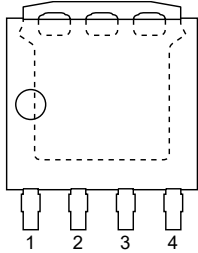
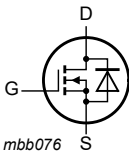
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| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|-------------------|--|-----|-----|-----|------|
| Dynamic characteristics | | | | | | |
| Q_{GD} | gate-drain charge | $I_D = 25\text{ A}$; $V_{DS} = 20\text{ V}$; $V_{GS} = 10\text{ V}$; | 2.8 | 9.3 | 19 | nC |
| $Q_{G(\text{tot})}$ | total gate charge | $T_j = 25\text{ °C}$; Fig. 12 ; Fig. 13 | 44 | 68 | 96 | nC |

[1] 240 A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--|---|
| 1 | S | source |  <p>LFPAK56E; Power-SO8 (SOT1023)</p> |  <p>mbb076</p> |
| 2 | S | source | | |
| 3 | S | source | | |
| 4 | G | gate | | |
| mb | D | mounting base; connected to drain | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------------------------|---------------------|---|-------------------------|
| | Name | Description | Version |
| PSMN1R4-40YSH | LFPAK56E; Power-SO8 | plastic, single-ended surface-mounted package (LFPAK56); 4 leads; 1.27 mm pitch | SOT1023 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|---------------|--------------|
| PSMN1R4-40YSH | 1H4S40Y |

8. Limiting values

Table 5. Limiting values

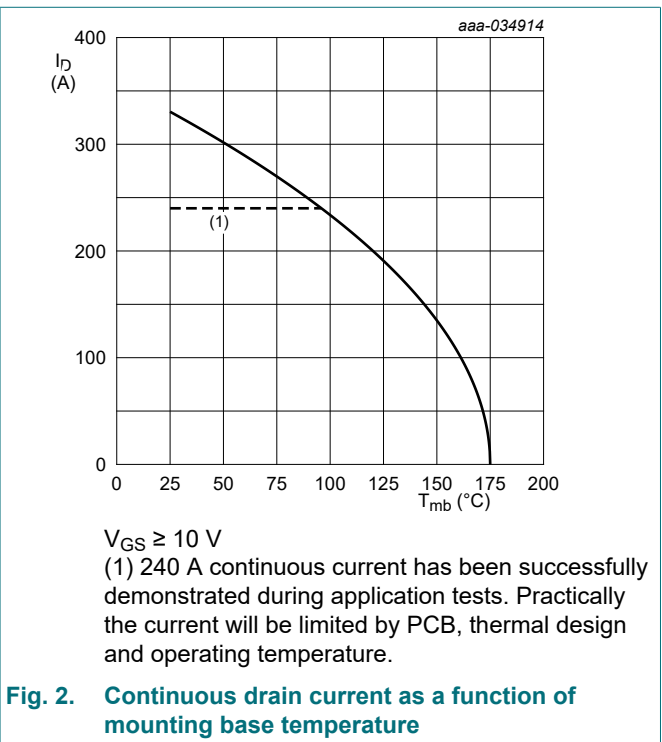
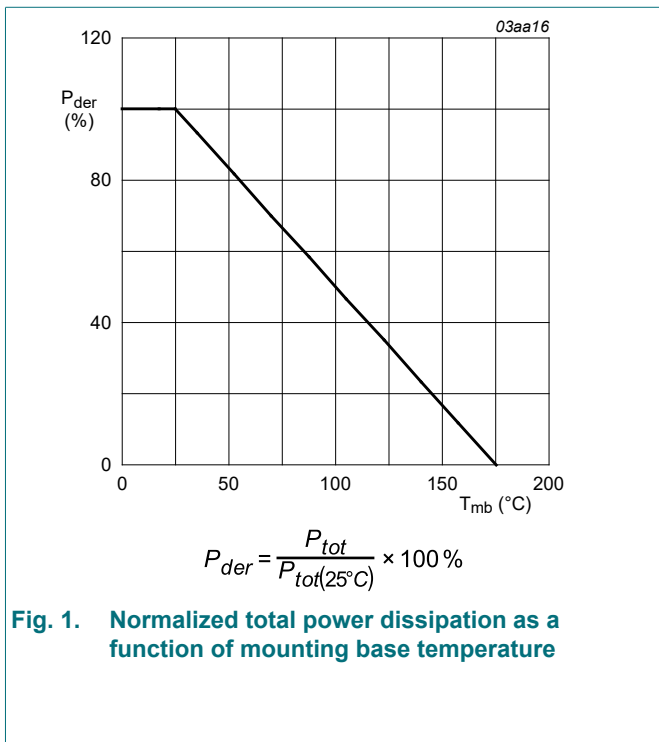
In accordance with the Absolute Maximum Rating System (IEC 60134). $T_j = 25\text{ °C}$ unless otherwise stated.

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------|---|-----|-----|------|
| V_{DS} | drain-source voltage | $25\text{ °C} \leq T_j \leq 175\text{ °C}$ | - | 40 | V |
| V_{DSM} | peak drain-source voltage | $t_p = 20\text{ ns}$; $f = 500\text{ kHz}$; $E_{DS(AL)} = 200\text{ nJ}$; pulsed | - | 45 | V |
| V_{DGR} | drain-gate voltage | $25\text{ °C} \leq T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$ | - | 40 | V |
| V_{GS} | gate-source voltage | | -20 | 20 | V |
| P_{tot} | total power dissipation | $T_{\text{mb}} = 25\text{ °C}$; Fig. 1 | - | 333 | W |

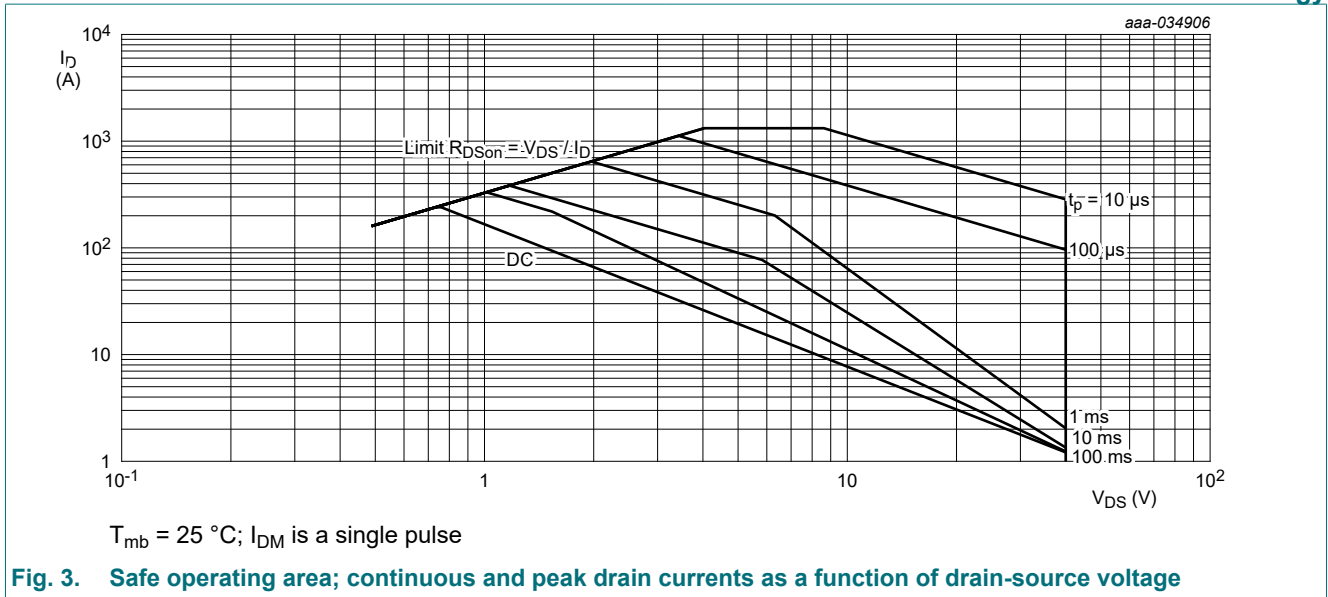
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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|-----------------------------|--|--|-----|-----|------|------|
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; Fig. 2 | [1] | - | 240 | A |
| | | V _{GS} = 10 V; T _{mb} = 100 °C; Fig. 2 | | - | 234 | A |
| I _{DM} | peak drain current | pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; Fig. 3 | | - | 1322 | A |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| T _j | junction temperature | | | -55 | 175 | °C |
| T _{slid(M)} | peak soldering temperature | | | - | 260 | °C |
| Source-drain diode | | | | | | |
| I _S | source current | T _{mb} = 25 °C | | - | 240 | A |
| I _{SM} | peak source current | pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C | | - | 1322 | A |
| Avalanche ruggedness | | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I _D = 71.2 A; V _{sup} ≤ 40 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped; t _p = 240 μs | [2] | - | 445 | mJ |
| | | I _D = 25 A; V _{sup} ≤ 40 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped; t _p = 2.69 ms | [2] | - | 1750 | mJ |
| I _{AS} | non-repetitive avalanche current | V _{sup} ≤ 40 V; V _{GS} = 10 V; T _{j(init)} = 25 °C; R _{GS} = 50 Ω | [2] | - | 190 | A |

- [1] 240 A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test



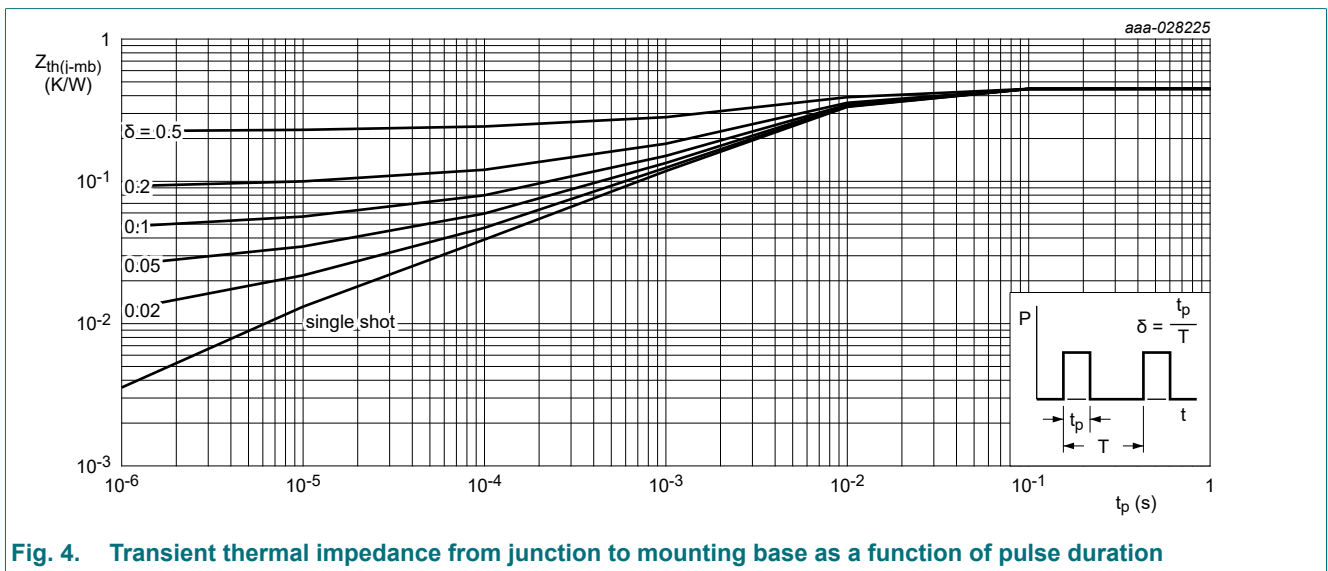
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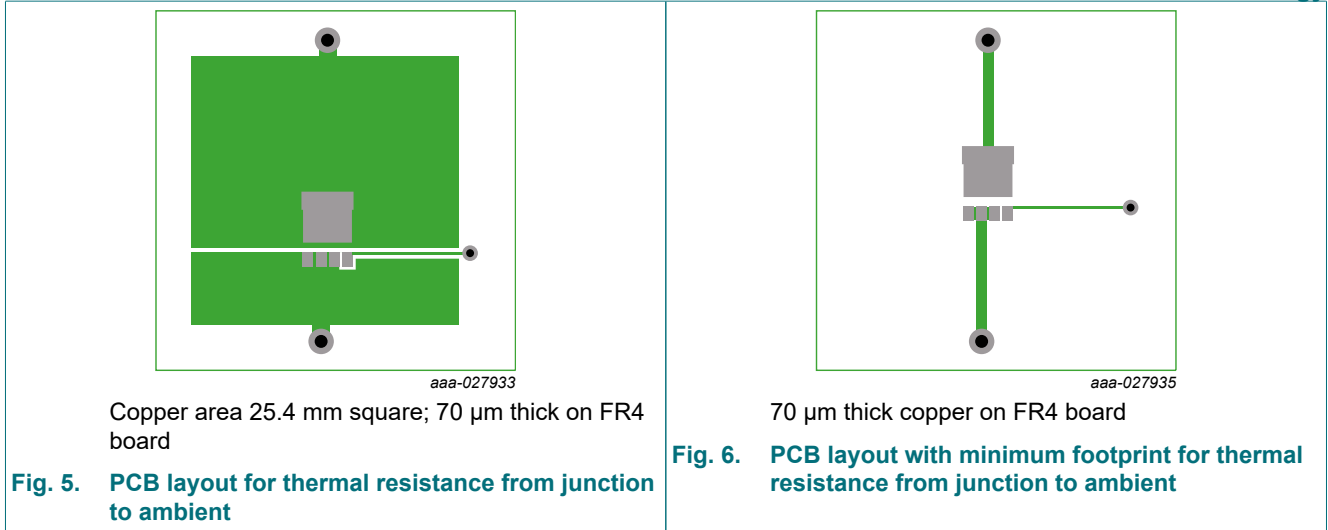
9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 4 | - | 0.33 | 0.45 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | Fig. 5 | - | 42 | - | K/W |
| | | Fig. 6 | - | 85 | - | K/W |



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10. Characteristics

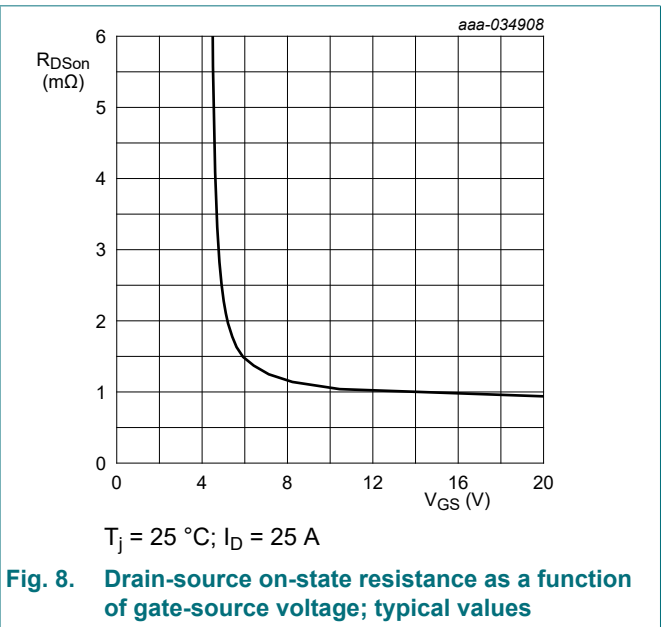
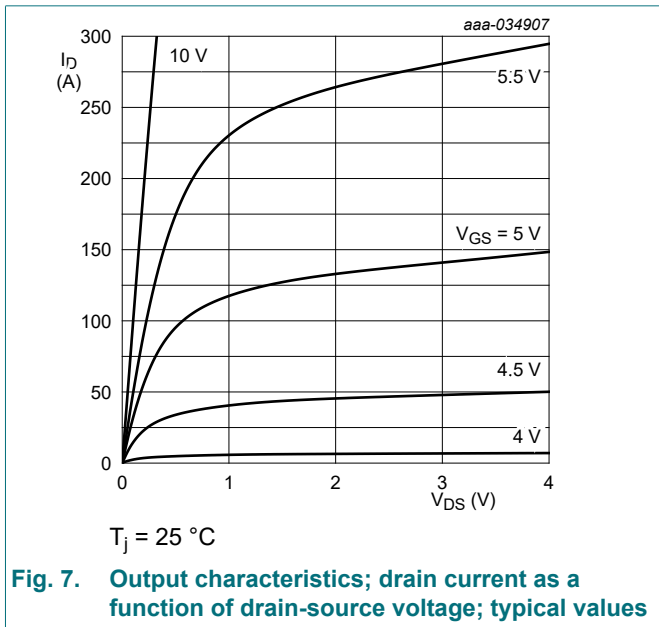
Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|--|---|-----|------|------|------------|
| Static characteristics | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$ | 40 | - | - | V |
| | | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$ | 36 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$ | 2.4 | 3.1 | 3.6 | V |
| $\Delta V_{GS(th)}/\Delta T$ | gate-source threshold voltage variation with temperature | $25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$ | - | -8 | - | mV/K |
| I_{DSS} | drain leakage current | $V_{DS} = 32 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$ | - | 0.01 | 1 | μA |
| | | $V_{DS} = 32 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$ | - | 3 | - | μA |
| I_{GSS} | gate leakage current | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$ | - | 2 | 100 | nA |
| | | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$ | - | 2 | 100 | nA |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ Fig. 10 | - | 1.06 | 1.4 | m Ω |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ C;$ Fig. 11 | - | - | 3.05 | m Ω |
| R_G | gate resistance | $f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$ | 0.4 | 1 | 2.5 | Ω |
| Dynamic characteristics | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ }^\circ C;$ Fig. 12 ; Fig. 13 | 44 | 68 | 96 | nC |
| | | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ }^\circ C$ | - | 35 | - | nC |
| Q_{GS} | gate-source charge | $I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ }^\circ C;$ Fig. 12 ; Fig. 13 | 13 | 22 | 33 | nC |
| $Q_{GS(th)}$ | pre-threshold gate-source charge | | 8.7 | 15 | 23 | nC |
| $Q_{GS(th-pl)}$ | post-threshold gate-source charge | | 4.2 | 7.1 | 11 | nC |
| Q_{GD} | gate-drain charge | | 2.8 | 9.3 | 19 | nC |
| $V_{GS(pl)}$ | gate-source plateau voltage | $I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; T_j = 25 \text{ }^\circ C;$ Fig. 12 ; Fig. 13 | - | 4.4 | - | V |

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| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------------|------------------------------|--|------|------|------|------|
| C_{iss} | input capacitance | $V_{DS} = 20\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$ | 3492 | 5373 | 7523 | pF |
| C_{oss} | output capacitance | $T_j = 25\text{ }^\circ\text{C};$ Fig. 14 | 885 | 1361 | 1905 | pF |
| C_{rss} | reverse transfer capacitance | | 70.5 | 235 | 517 | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS} = 20\text{ V}; R_L = 0.8\text{ }\Omega; V_{GS} = 10\text{ V};$ | - | 19 | - | ns |
| t_r | rise time | $R_{G(ext)} = 5\text{ }\Omega; T_j = 25\text{ }^\circ\text{C}$ | - | 14 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 39 | - | ns |
| t_f | fall time | | - | 16 | - | ns |
| Q_{oss} | output charge | $V_{GS} = 0\text{ V}; V_{DS} = 20\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^\circ\text{C}$ | - | 46 | - | nC |
| Source-drain diode | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 15 | - | 0.77 | 1 | V |
| t_{rr} | reverse recovery time | $I_S = 25\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$ | - | 36 | - | ns |
| Q_r | recovered charge | $V_{DS} = 20\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 16 | [1] | 34 | - | nC |
| t_a | reverse recovery rise time | | - | 20 | - | ns |
| t_b | reverse recovery fall time | | - | 16 | - | ns |

[1] includes capacitive recovery



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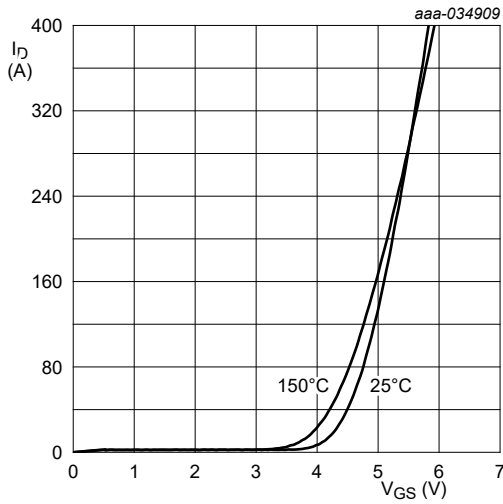


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

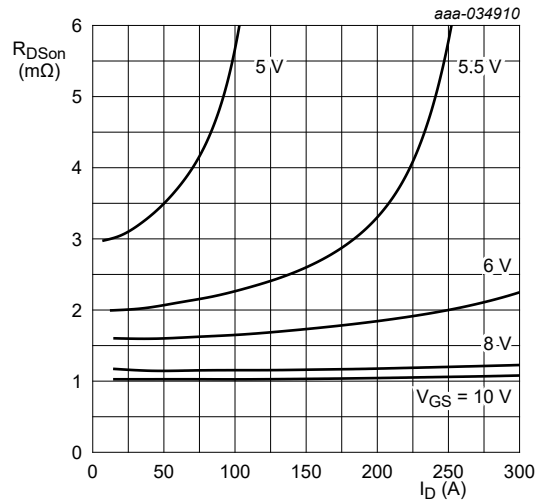
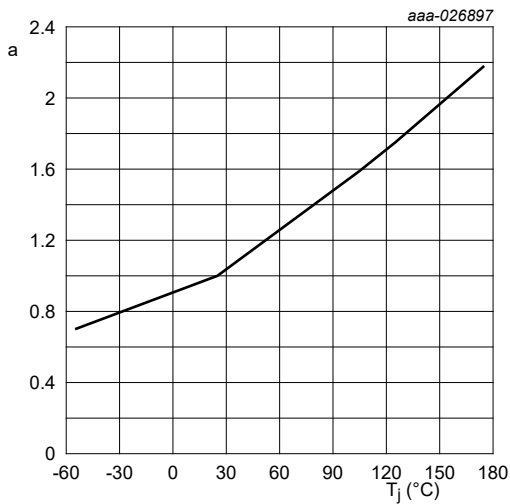


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

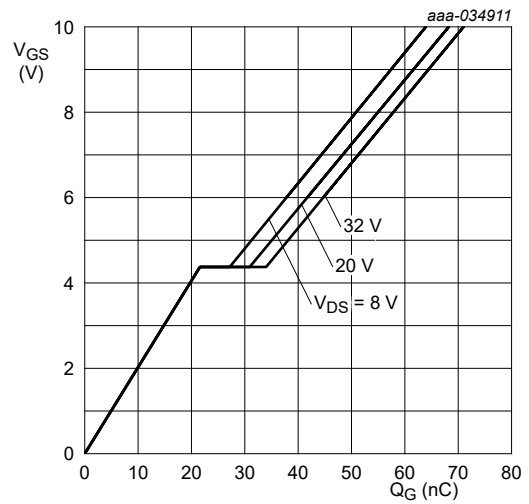


Fig. 12. Gate-source voltage as a function of gate charge; typical values

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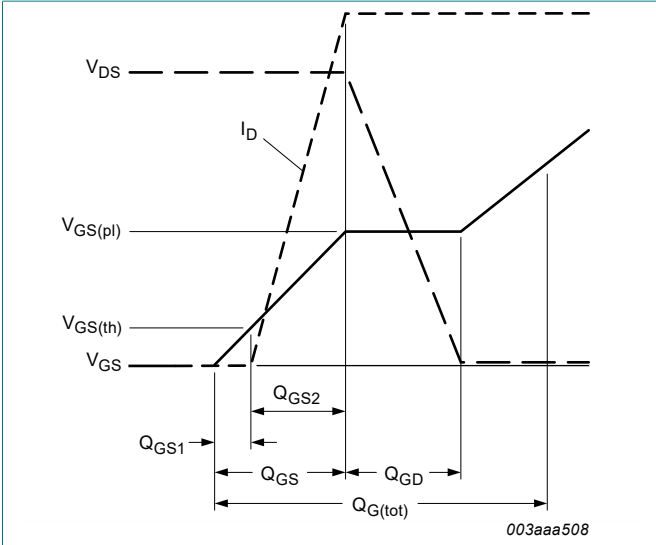


Fig. 13. Gate charge waveform definitions

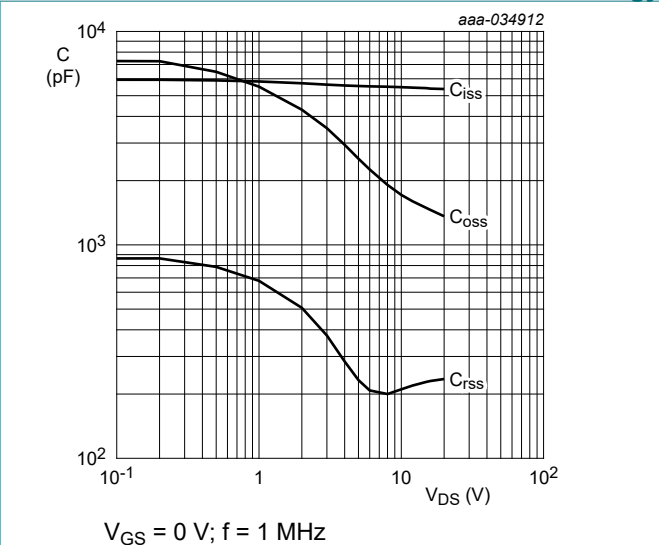


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

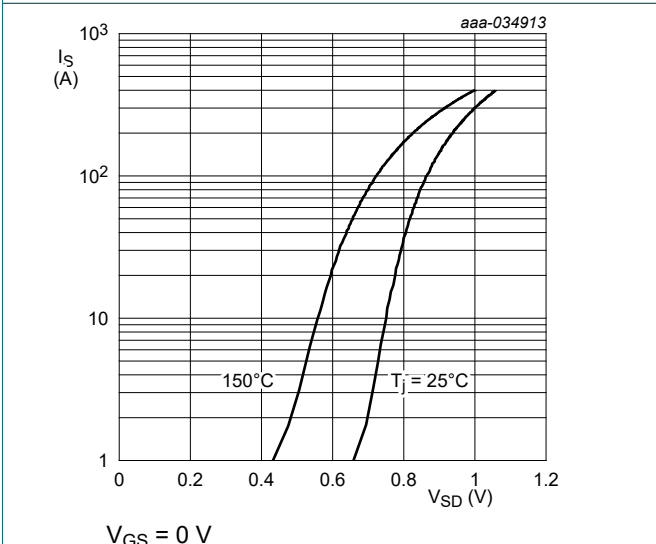


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

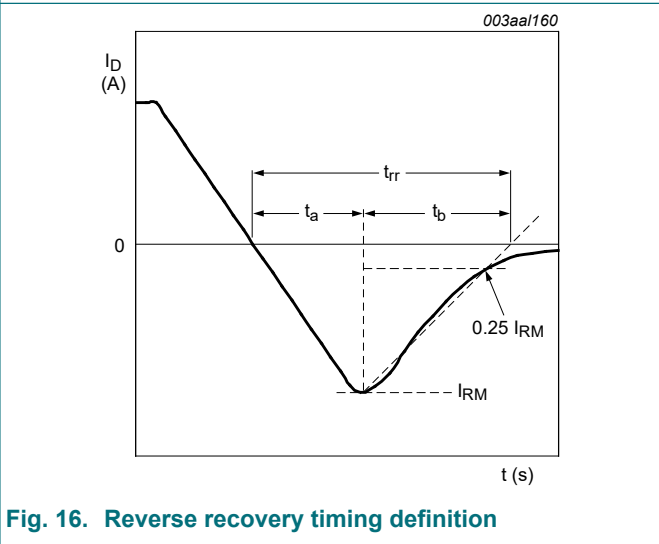


Fig. 16. Reverse recovery timing definition

11. Package outline

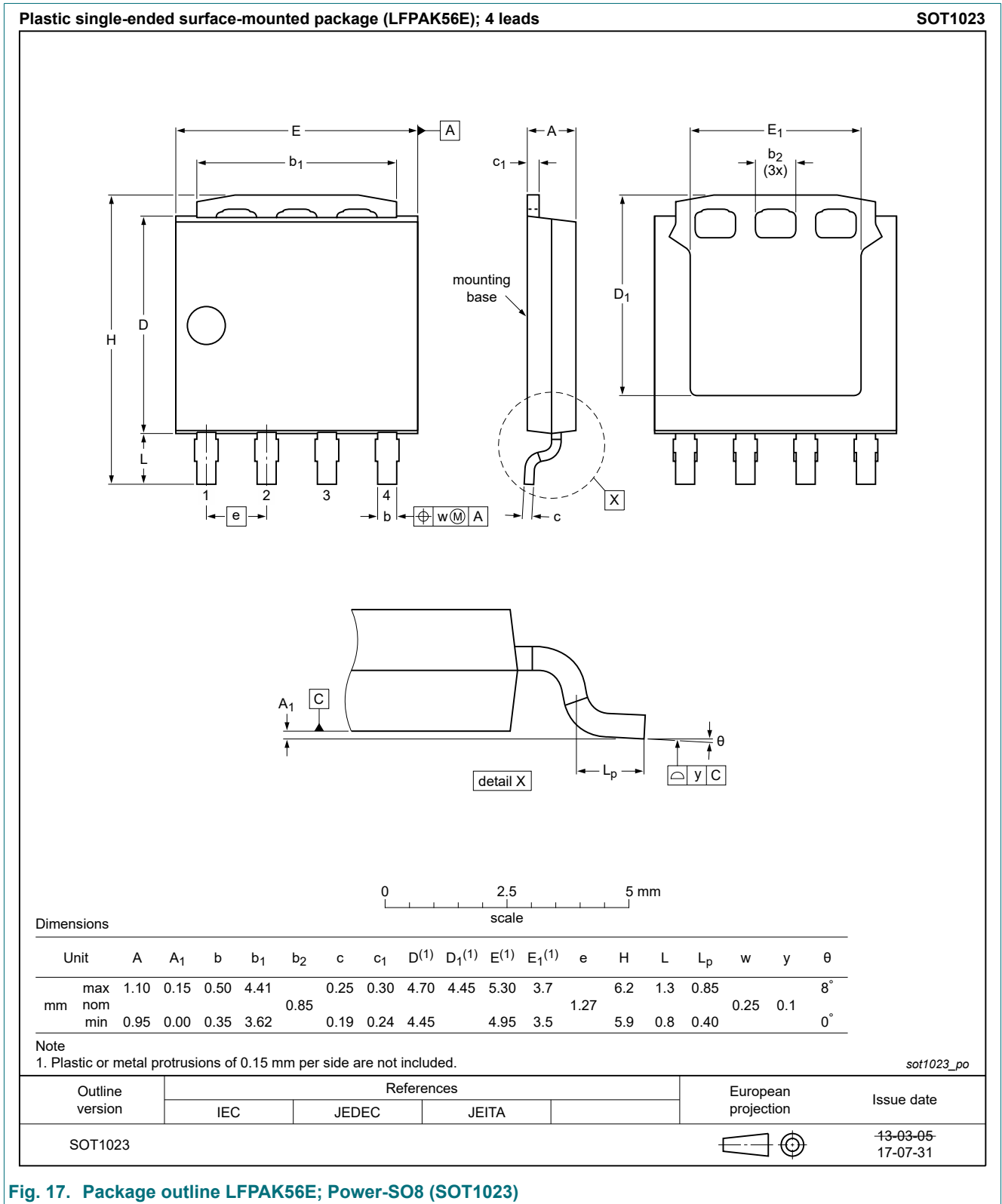


Fig. 17. Package outline LPAK56E; Power-SO8 (SOT1023)

12. Soldering

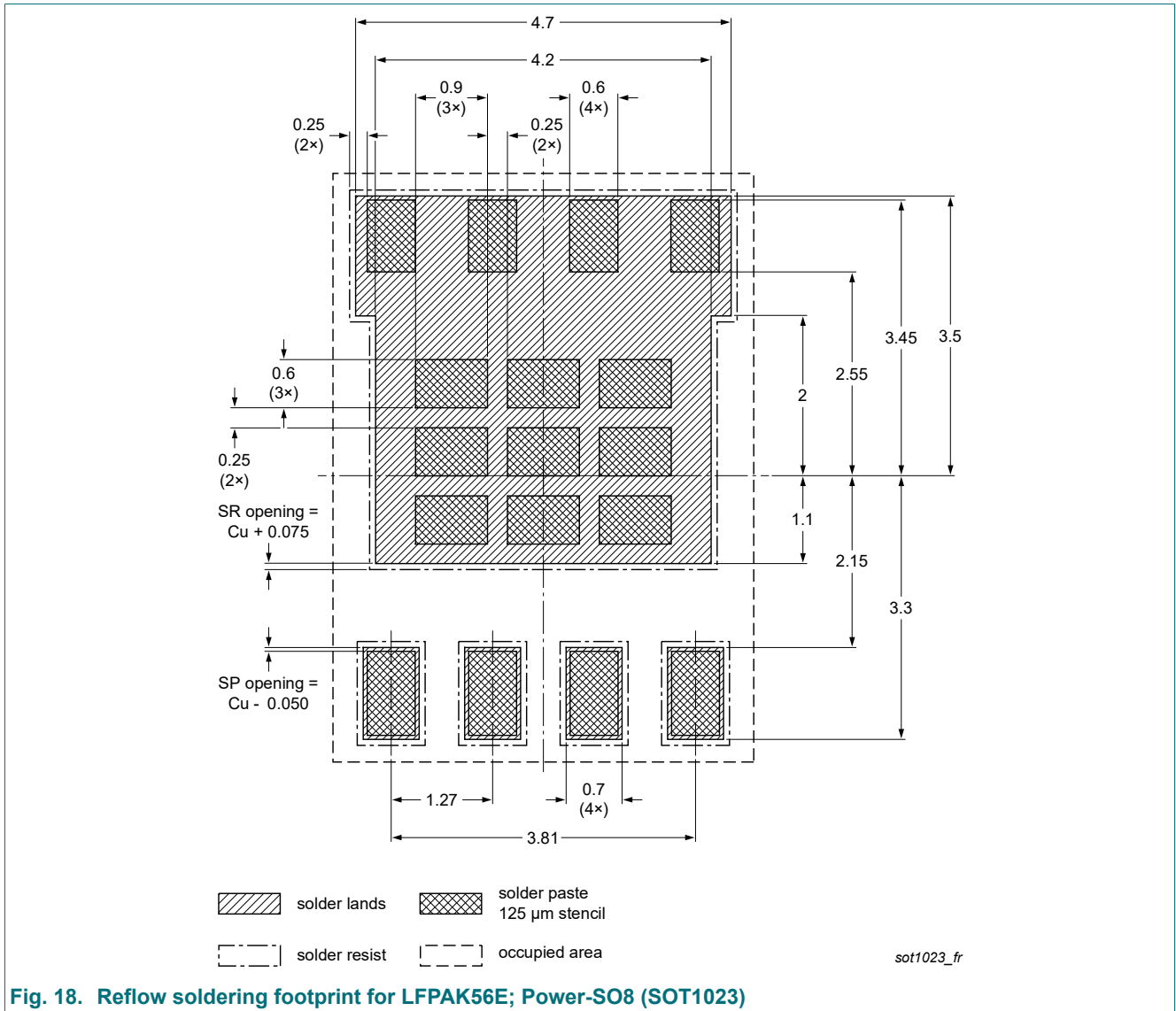


Fig. 18. Reflow soldering footprint for LPAK56E; Power-SO8 (SOT1023)

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13. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
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Contents

| | |
|---------------------------------|----|
| 1. General description..... | 1 |
| 2. Features and benefits..... | 1 |
| 3. Applications..... | 1 |
| 4. Quick reference data..... | 1 |
| 5. Pinning information..... | 2 |
| 6. Ordering information..... | 2 |
| 7. Marking..... | 2 |
| 8. Limiting values..... | 2 |
| 9. Thermal characteristics..... | 4 |
| 10. Characteristics..... | 5 |
| 11. Package outline..... | 9 |
| 12. Soldering..... | 10 |
| 13. Legal information..... | 11 |

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